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1. (Original) A semiconductor device including a gate portion comprising a semiconductor film disposed at a predetermined region on the surface of a semiconductor substrate, and

source and drain regions comprising an impurity introduced layer formed by introducing impurities selectively to the inside of the semiconductor substrate, wherein

the gate portion and a region just below the gate portion are not melted by the irradiation of a laser light and the impurity introduced layer comprises a melted and re-solidified layer.

2. (Original) A semiconductor device according to claim 1, wherein the semiconductor substrate is mounted on an insulation film.

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3. (Original) A semiconductor device according to claim 1, wherein an insulated gate field effect transistor and a bipolar transistor are formed on one identical semiconductor substrate.

4. (Original) A semiconductor device according to claim 1, wherein at least one kind of a semiconductor film, a SILICON silicide film or a metal film is present between the source and drain regions and electrodes for electrically connecting the regions.

5. (Original) A semiconductor device including a gate portion comprising a semiconductor film disposed at a predetermined region on the surface of a semiconductor substrate, and

source and drain regions comprising an impurity introduced layer formed by introducing impurities selectively to the inside of the semiconductor substrate by using the semiconductor film as a mask, wherein

the impurity introduced layer comprises an impurity layer having a box shaped highly doped impurity distribution on at least one cross section perpendicular to the main surface of the semiconductor substrate.

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6. (Original) A semiconductor device according to claim 5, wherein the semiconductor substrate is mounted on an insulation film.

7. (Original) A semiconductor device according to claim 5, wherein an insulated gate field effect transistor and a bipolar transistor are formed on one identical semiconductor substrate.

8. (Original) A semiconductor device according to claim 5, wherein at least one kind of a semiconductor film, a SILICON silicide film or a metal film is present between the source and drain regions and electrodes for electrically connecting the regions.

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9. (Original) A semiconductor device including:

a first region having a first conduction type formed in a semiconductor substrate;

a second region having a second conduction type disposed adjacent with the first region;

a gate portion comprising a semiconductor film disposed to a predetermined region on the first region;

source and drain regions comprising a first impurity introduced layer formed by introducing impurities having a second conduction type selectively to the first region by using the semiconductor film as a mask;

a gate portion comprising a semiconductor film disposed to a predetermined region on the second region; and

source and drain regions comprising a second impurity introduced layer formed by introducing impurities having a first conduction type selectively to the second region by using the semiconductor film as a mask, wherein

the first and the second impurity introduced layers each comprises an impurity layer having a box shaped highly doped impurity distribution on at least one cross section perpendicular to the main surface of the semiconductor substrate.

10. (Original) A semiconductor device according to claim 9, wherein the semiconductor substrate is mounted on an insulation film.

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11. (Original) A semiconductor device according to claim 9, wherein an insulated gate field effect transistor and a bipolar transistor are formed on one identical semiconductor substrate.

12. (Original) A semiconductor device according to claim 9, wherein at least one kind of a semiconductor film, a SILICON silicide film or a metal film is present between the source and drain regions and electrodes for electrically connecting the regions.

CLAIMS 13 – 48 (CANCELLED)